

Electrostatic Discharged Protection Devices (ESD) Data Sheet

Description

Brightking's UDT23AXXL02 series are ultra low capacitance TVS arrays designed to protect high speed data interfaces. This series has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from overvoltage caused by electrostatic discharge (ESD), cable discharge events(CDE) and electrical fast transients(EFT).The series has a typical capacitance of only 0.8pF. This means it can be used on circuits operating in excess of 3GHz without signal attenuation.

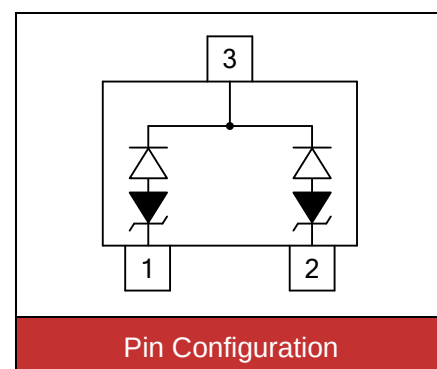


Contact : $\pm 30\text{kV}$
Air : $\pm 30\text{kV}$



Features

- IEC61000-4-2 ESD 30KV Air, 30KV contact compliance
- SOT-23 surface mount package
- Protects two high speed data line
- Peak power dissipation of 400W under 8/20 μs waveform
- Working voltage: 3.3V, 5V, 12V, 15V and 24V
- Low leakage current
- Ultra low capacitance and clamping voltage
- Solid-state silicon avalanche technology
- Lead Free/RoHS compliant
- Solder reflow temperature: Pure Tin-Sn, 260~270°C
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020



Applications

- HDMI interface protection
- Mobile display digital interface
- RF/Antenna circuits
- USB 2.0 & Firewire ports
- GaAs photodetector protection
- HBT power Amp protection
- Infiniband transceiver protection

Maximum Ratings

Rating	Symbol	Value	Unit
Peak pulse power (tp=8/20 μs waveform)	P_{PP}	400	W
ESD voltage (Contact discharge)	V_{ESD}	± 30	kV
ESD voltage (Air discharge)		± 30	
Storage & operating temperature range	T_{STG}, T_J	-55~+150	°C

Electrical Characteristics ($T_J=25^{\circ}\text{C}$)
UDT23A03L02 (Marking: B LSC)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				3.3	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1\text{mA}$	4			V
Reverse leakage current	I_R	$V_R=3.3\text{V}$ each I/O pin			20	μA
Clamping voltage ($t_p=8/20\mu\text{s}$)	V_C	$I_{PP}=1\text{A}$			10	V
Peak Pulse Current ($t_p=8/20\mu\text{s}$)	I_{PP}				19	A
Off state junction capacitance	C_J	0Vdc, $f=1\text{MHz}$ Between I/O pins and GND		1.5		pF

UDT23A05L02 (Marking: B LTC)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				5	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1\text{mA}$	6			V
Reverse leakage current	I_R	$V_R=5\text{V}$ each I/O pin			5	μA
Clamping voltage ($t_p=8/20\mu\text{s}$)	V_C	$I_{PP}=1\text{A}$			12	V
Peak Pulse Current ($t_p=8/20\mu\text{s}$)	I_{PP}				17	A
Off state junction capacitance	C_J	0Vdc, $f=1\text{MHz}$ Between I/O pins and GND		0.8		pF

UDT23A12L02 (Marking: B LUC)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				12	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1\text{mA}$	13.3			V
Reverse leakage current	I_R	$V_R=12\text{V}$ each I/O pin			1	μA
Clamping voltage ($t_p=8/20\mu\text{s}$)	V_C	$I_{PP}=1\text{A}$			25	V
Peak Pulse Current ($t_p=8/20\mu\text{s}$)	I_{PP}				10	A
Off state junction capacitance	C_J	0Vdc, $f=1\text{MHz}$ Between I/O pins and GND		0.8		pF

UDT23A15L02 (Marking: B LWC)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				15	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1\text{mA}$	16.7			V
Reverse leakage current	I_R	$V_R=15\text{V}$ each I/O pin			1	μA
Clamping voltage ($t_p=8/20\mu\text{s}$)	V_C	$I_{PP}=1\text{A}$			30	V
Peak Pulse Current ($t_p=8/20\mu\text{s}$)	I_{PP}				8	A
Off state junction capacitance	C_J	0Vdc, $f=1\text{MHz}$ Between I/O pins and GND		0.8		pF

Electrical Characteristics ($T_J=25^{\circ}\text{C}$)

UDT23A24L02 (Marking: B LXC)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				24	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1\text{mA}$	26.7			V
Reverse leakage current	I_R	$V_R=24\text{V}$ each I/O pin			1	μA
Clamping voltage ($t_p=8/20\mu\text{s}$)	V_C	$I_{PP}=1\text{A}$			48	V
Peak Pulse Current ($t_p=8/20\mu\text{s}$)	I_{PP}				6	A
Off state junction capacitance	C_J	0Vdc, $f=1\text{MHz}$ Between I/O pins and GND		0.8		pF

Typical Characteristics Curves

Figure 1. Power Derating Curve

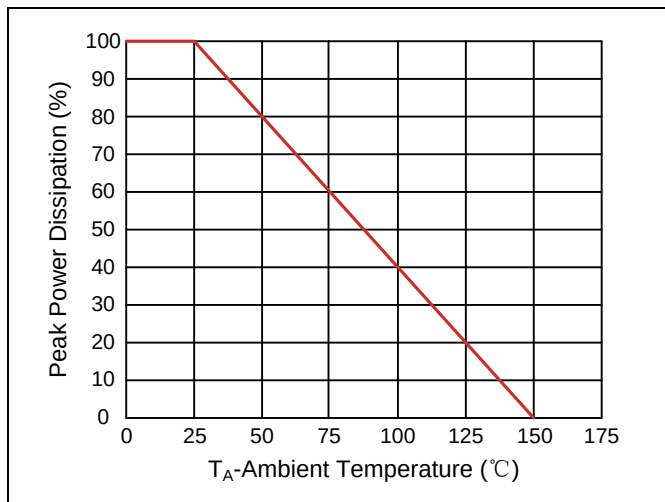


Figure 2. Pulse Waveforms

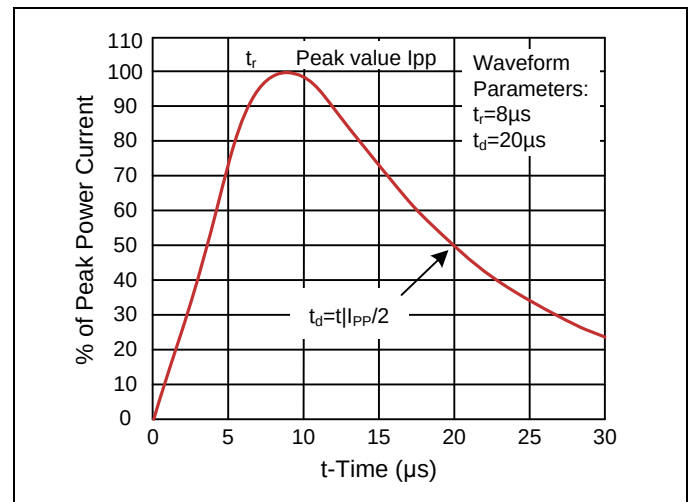


Figure 3. Non-Repetitive Peak Pulse vs. Pulse Time

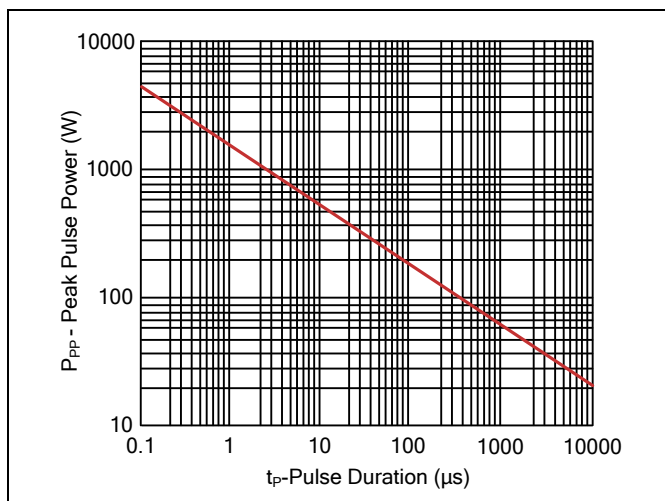
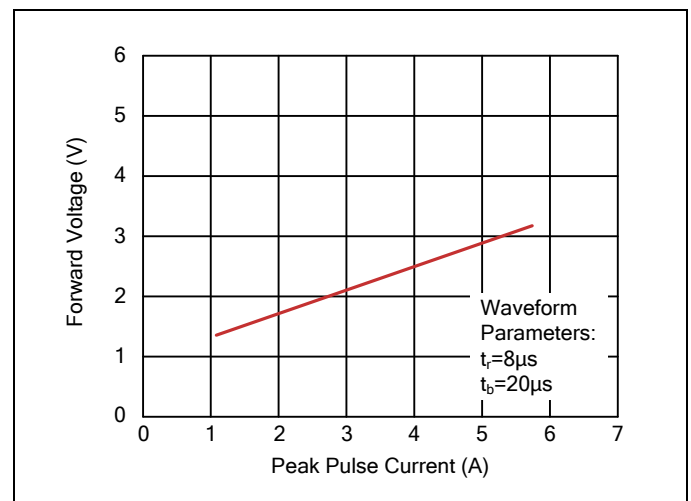
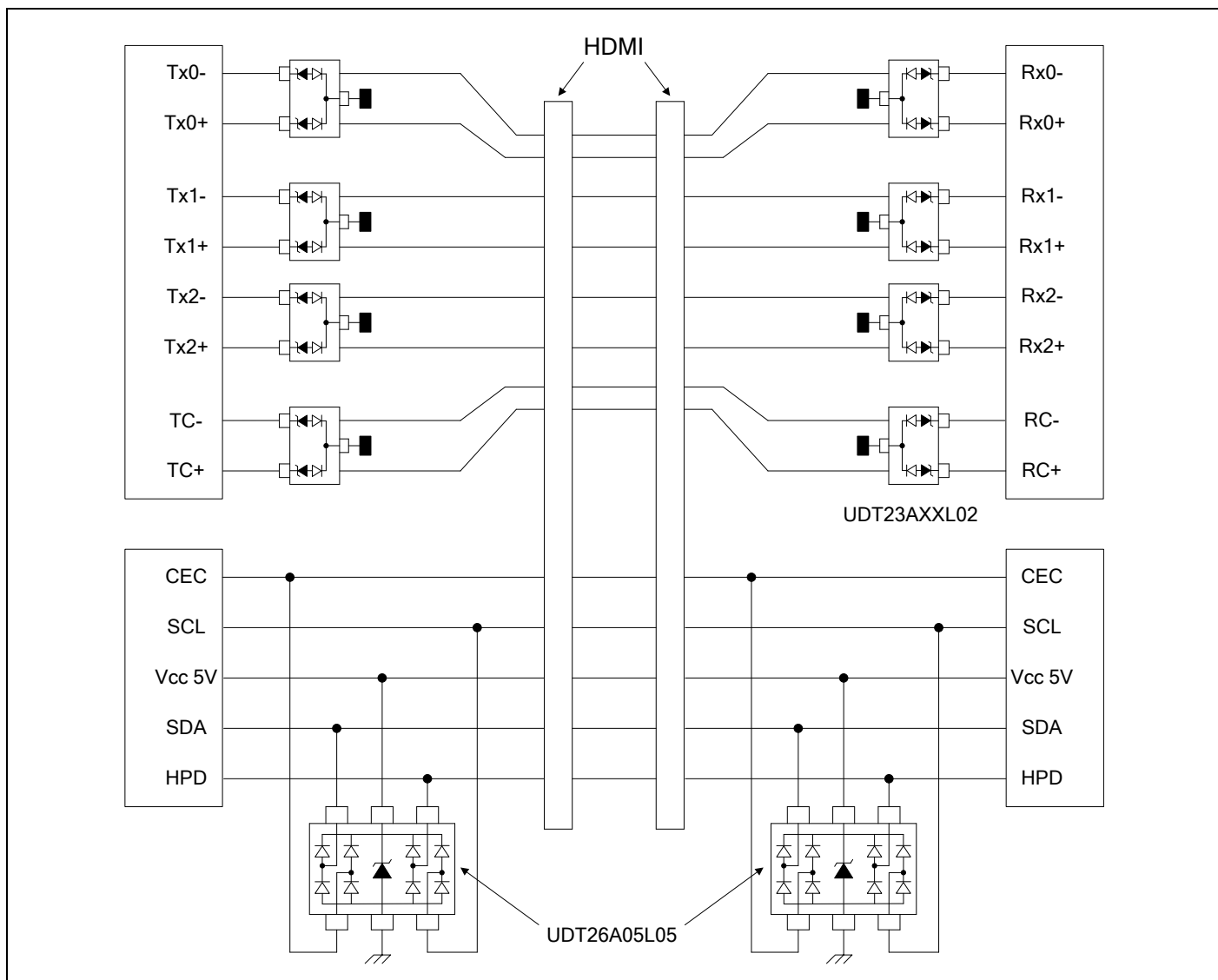


Figure 4. Forward Voltage vs. Forward Current

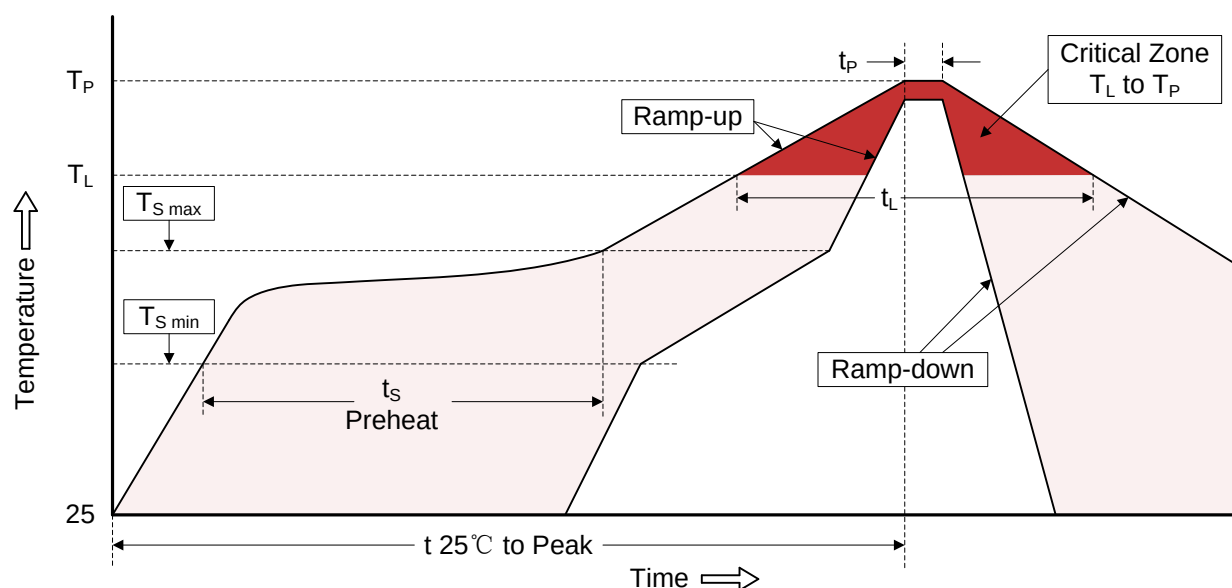


Applications Information



Recommended Soldering Conditions

Reflow Soldering

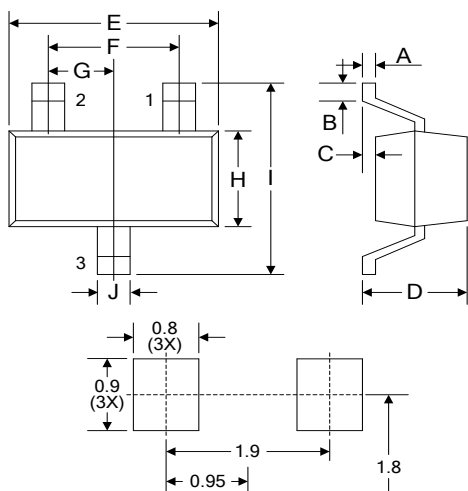


Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.
Preheat -Temperature Min ($T_{S\ min}$) -Temperature Max ($T_{S\ max}$) -Time (min to max) (t_s)	150°C 200°C 60-180 seconds
$T_{S\ max}$ to T_L -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature (T_L) -Time (t_L)	217°C 60-150 seconds
Peak Temperature (T_P)	260°C
Time within 5°C of actual Peak Temperature (t_P)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Dimensions (SOT-23)

Symbol	Dimension			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.08	0.18	0.003	0.007
B	0.15	-	0.006	-
C	-	0.13	-	0.005
D	0.89	1.09	0.035	0.043
E	2.80	3.05	0.110	0.120
F	1.90		0.075	
G	0.95		0.037	
H	1.19	1.40	0.047	0.055
I	2.10	2.49	0.083	0.098
J	0.35	0.50	0.014	0.020



Recommended Soldering Pad Layout

Packaging

Tape		Symbol	Dimension (mm)
		W	8.00±0.30
		P0	4.00±0.10
		P1	4.00±0.10
		P2	2.00±0.10
		D0	Φ1.55±0.10
		D1	Φ1.00±0.05
		E	1.75±0.10
		F	3.50±0.10
		A	3.10±0.10
		A0	2.10±0.10
		B	2.75±0.10
		B0	0.65±0.10
		K	1.10±0.10
		t	0.20±0.05
Reel		D	Φ178.0±2.0
		D2	Φ13.0
		W1	9.5
		Quantity: 3000PCS	